

Abstract of the Disclosure

A semiconductor light emitting device including means for reducing strain and carrier overflow caused by injection of a number of carriers in semiconductor light emitting devices using GaN is provided. The semiconductor light emitting device includes a multi-quantum barrier formed by depositing an AlGaN/GaN double layer a predetermined number of times, or a strain-compensating multiple quantum barrier formed at either the upper or lower sides of an active layer by depositing an AlGaN/InGaN double layer a predetermined number of times, and does not need a p-type clad layer.